

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	8	-6	A
Pulsed Drain Current (Note 1)	I_{DM}	25	-20	A
Maximum Power Dissipation	P_D	2.5	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note2)	$R_{\theta JA}$	N-Ch	89	°C/W
		P-Ch	90	

N-CH Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=6A$	-	17	21	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	-	24	31	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$	-	480	-	PF
Output Capacitance	C_{oss}		-	80	-	PF
Reverse Transfer Capacitance	C_{rss}		-	60	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5A, V_{GS}=10V$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.85	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=3A$	-	-	1.3	V
Diode Forward Current (Note 2)	I_S		-	-	4	A



TECH PUBLIC

台湾电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

WWW.TECHPUBLIC.COM

N- Channel Typical Electrical and Thermal Characteristics (Curves)

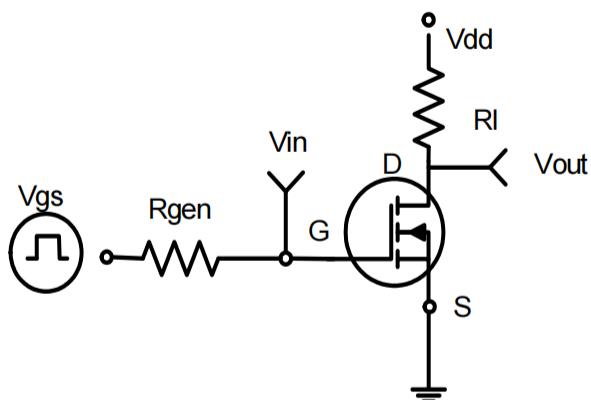


Figure 1:Switching Test Circuit

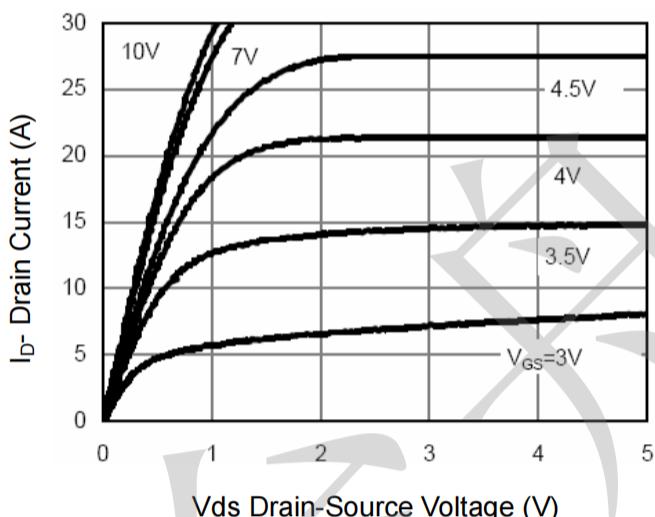


Figure 3 Output Characteristics

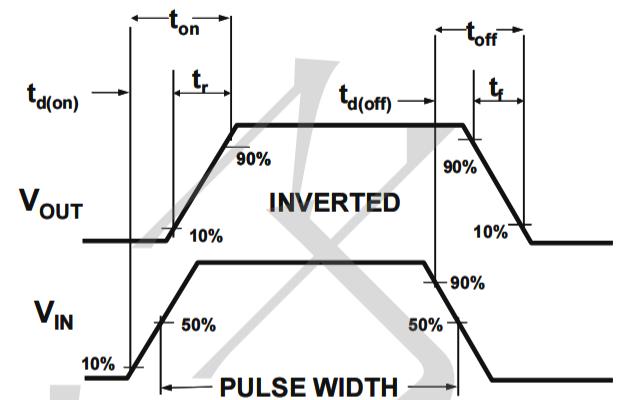


Figure 2:Switching Waveforms

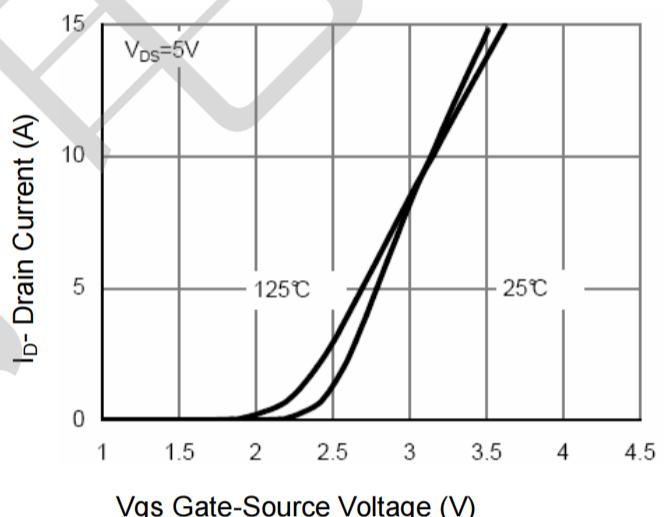
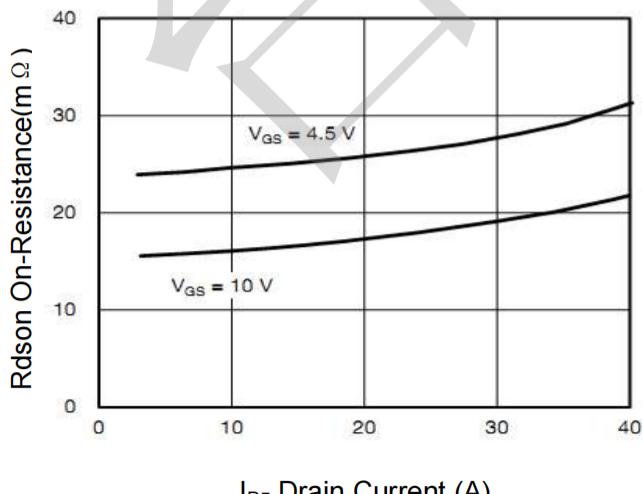
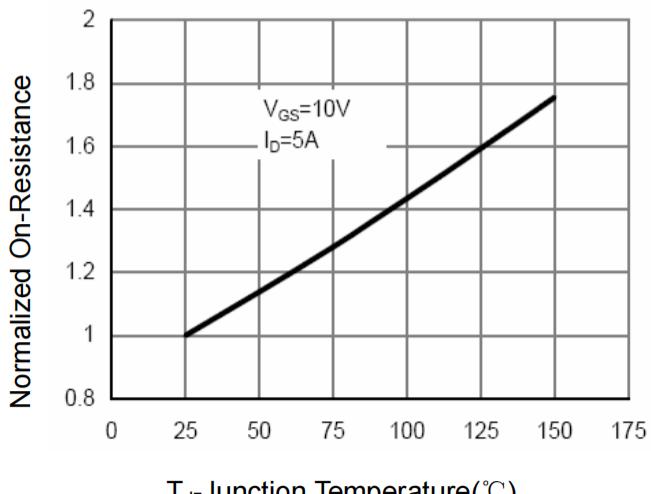


Figure 4 Transfer Characteristics



I_D- Drain Current (A)

Figure 5 Drain-Source On-Resistance



T_J-Junction Temperature(°C)

Figure 6 Drain-Source On-Resistance



TECH PUBLIC

台湾电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

WWW.TECHPUBLIC.COM

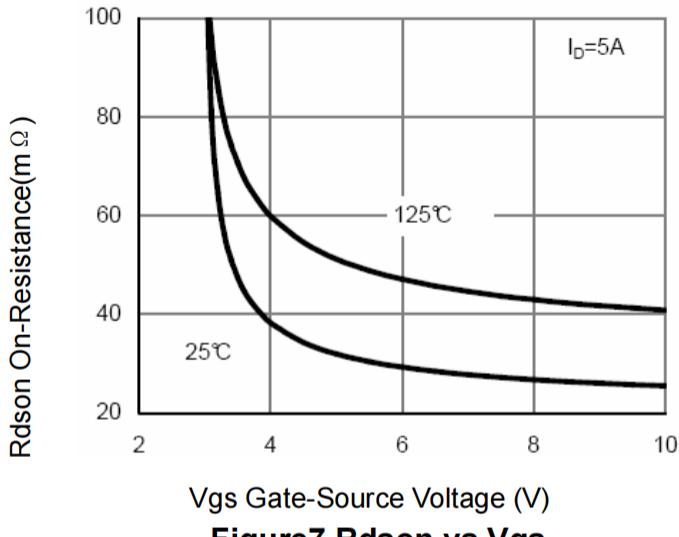


Figure 7 $R_{DS(on)}$ vs V_{GS}

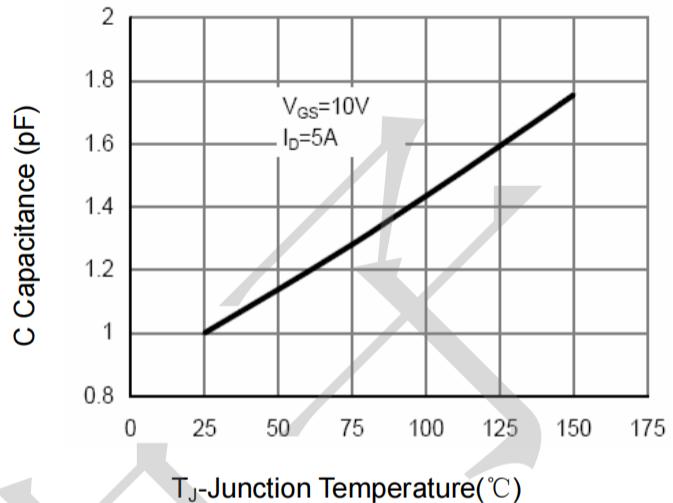


Figure 8 Drain-Source On-Resistance

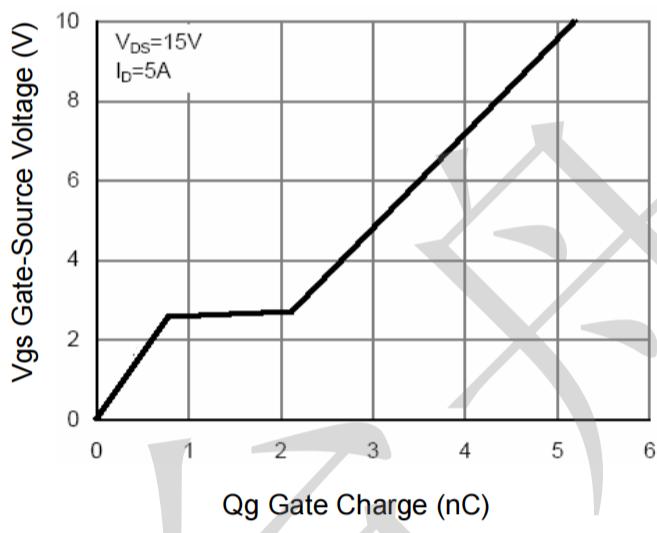


Figure 9 Gate Charge

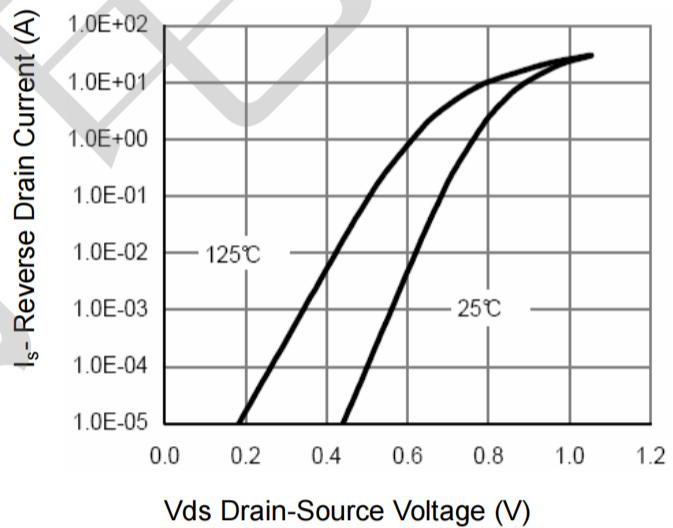


Figure 10 Source-Drain Diode Forward

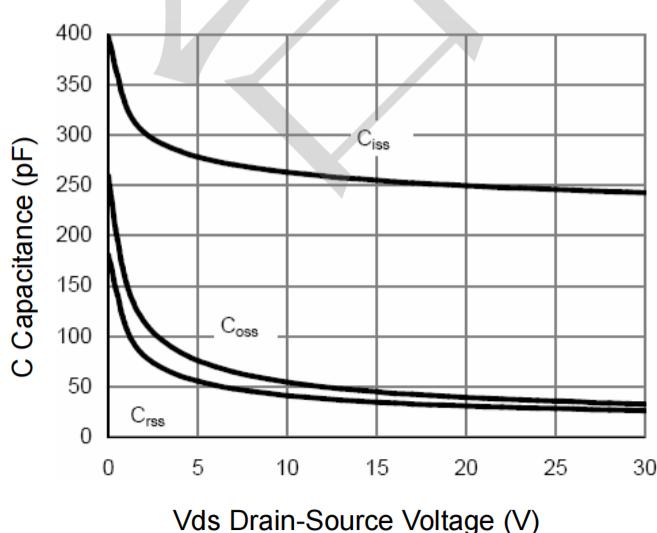


Figure 11 Capacitance vs V_{DS}

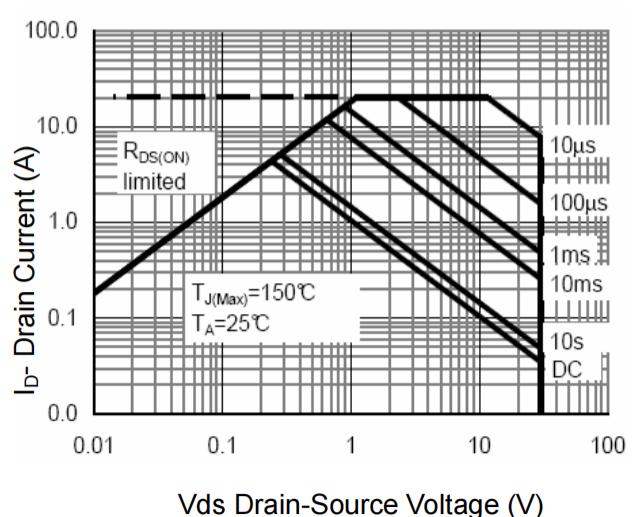


Figure 12 Safe Operation Area



TECH PUBLIC

台舟电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

WWW.TECHPUBLIC.COM

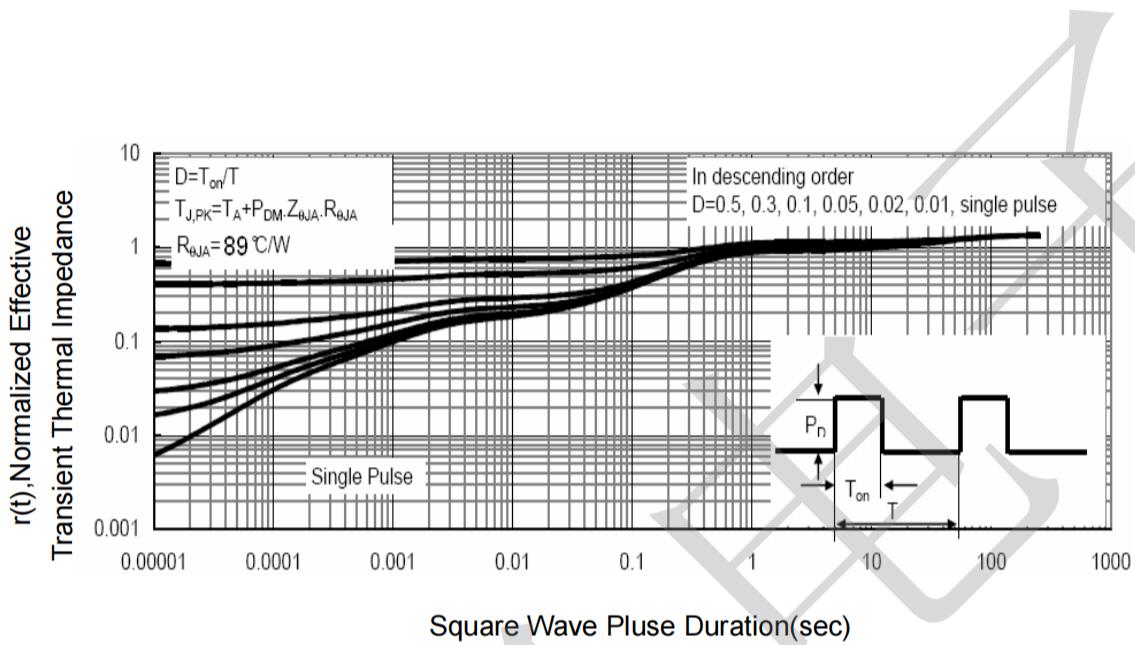


Figure 13 Normalized Maximum Transient Thermal Impedance

P-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-24\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.5	-2	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	40	50	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	60	75	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-4.1\text{A}$	5.5	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	648	-	PF
Output Capacitance	C_{oss}		-	108	-	PF
Reverse Transfer Capacitance	C_{rss}		-	68	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, R_{\text{L}}=3.6\Omega$ $V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$	-	9	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	13.5	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4\text{A}, V_{\text{GS}}=-10\text{V}$	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	3.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3.	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1\text{A}$	-	-	-1.3	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



TECH PUBLIC

台湾电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

P-Channel Typical Electrical and Thermal Characteristics

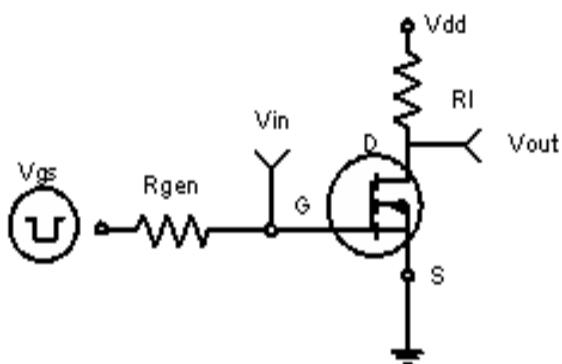


Figure 1:Switching Test Circuit

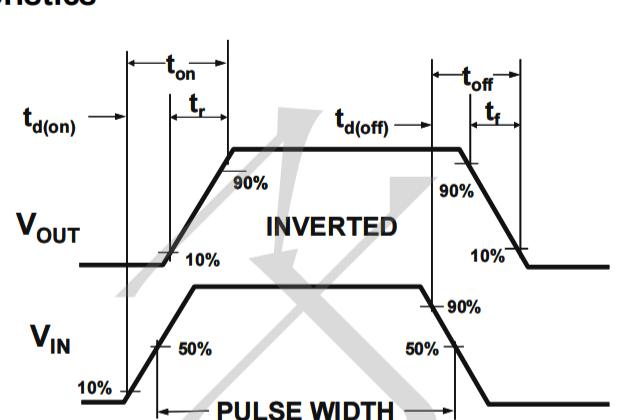


Figure 2:Switching Waveforms

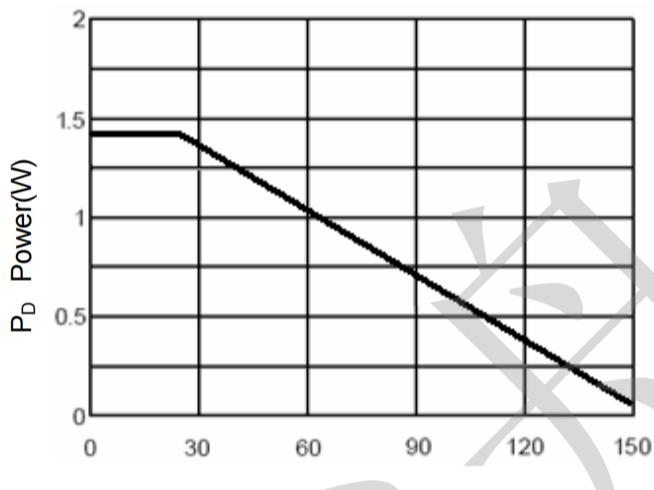


Figure 3 Power Dissipation

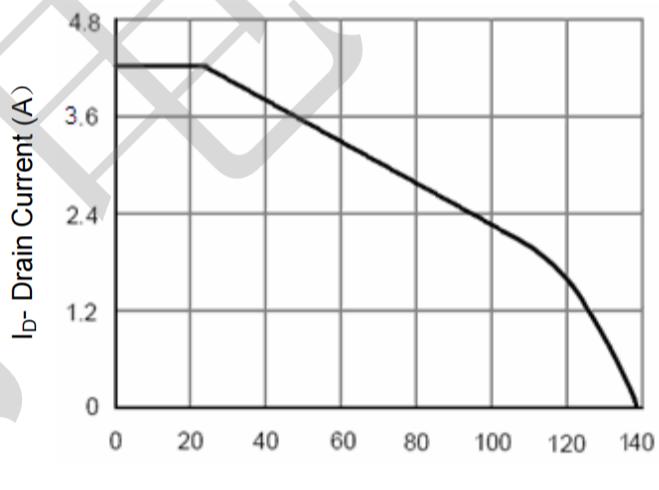


Figure 4 Drain Current

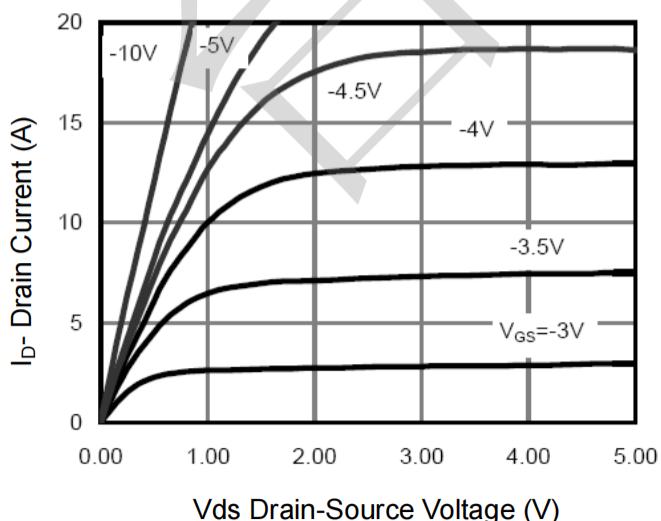


Figure 5 Output CHARACTERISTICS

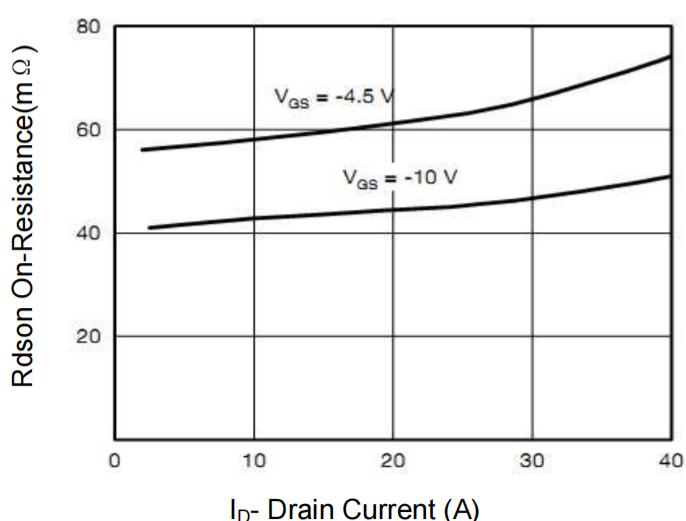


Figure 6 Drain-Source On-Resistance



TECH PUBLIC

台湾电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

WWW.TECHPUBLIC.COM

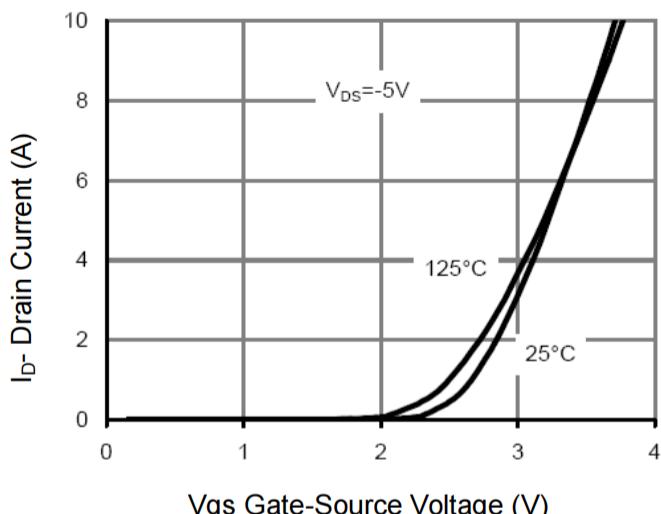


Figure 7 Transfer Characteristics

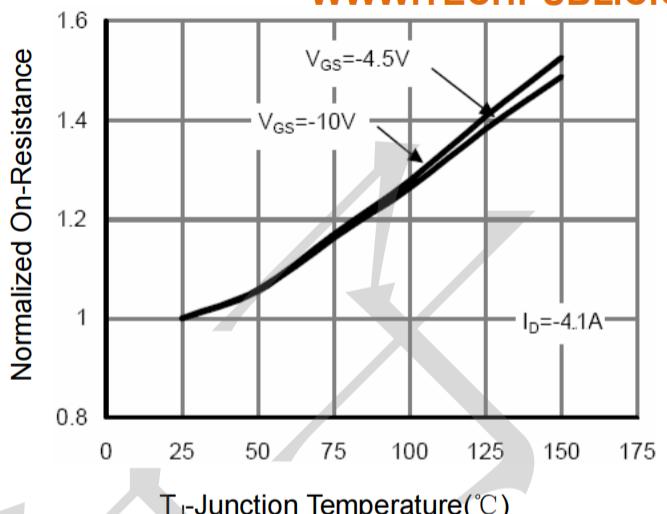


Figure 8 Drain-Source On-Resistance

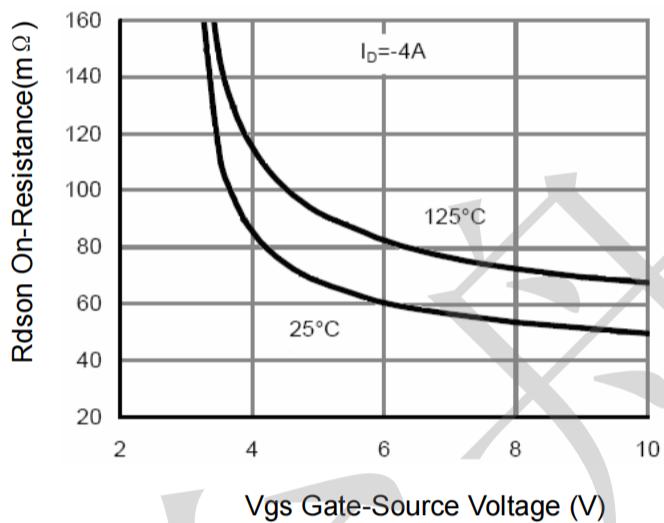


Figure 9 $R_{DS(on)}$ vs V_{GS}

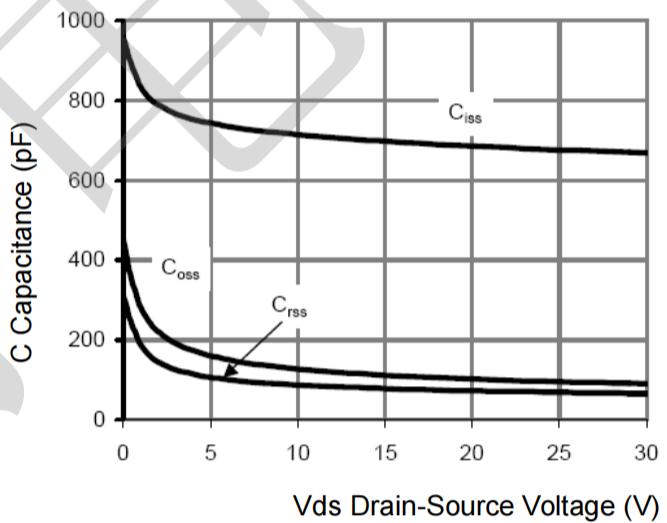


Figure 10 Capacitance vs V_{DS}

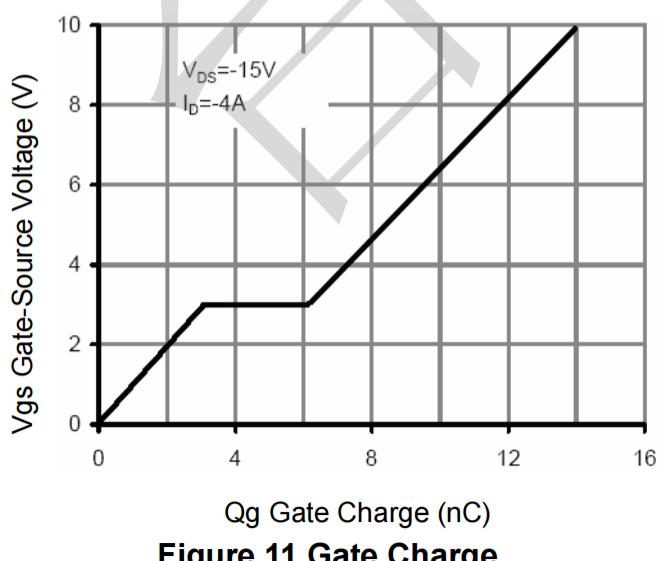


Figure 11 Gate Charge

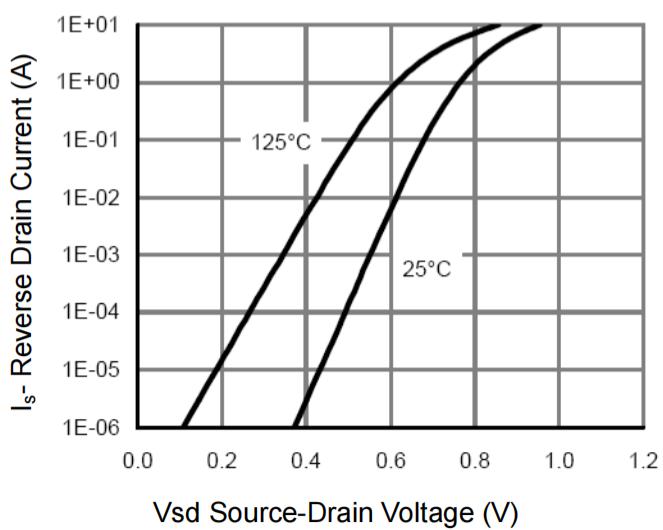


Figure 12 Source-Drain Diode Forward



TECH PUBLIC

台舟电子

IRF9952TRPBF-TP

N&P-Channel Complementary MOSFET

WWW.TECHPUBLIC.COM

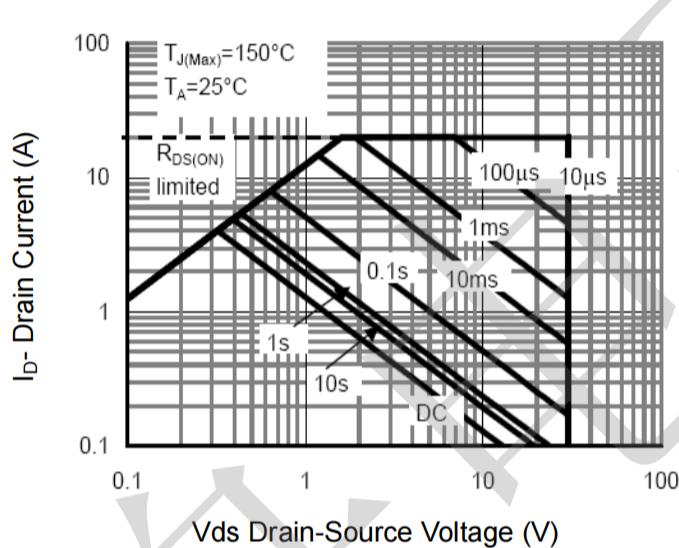


Figure 13 Safe Operation Area

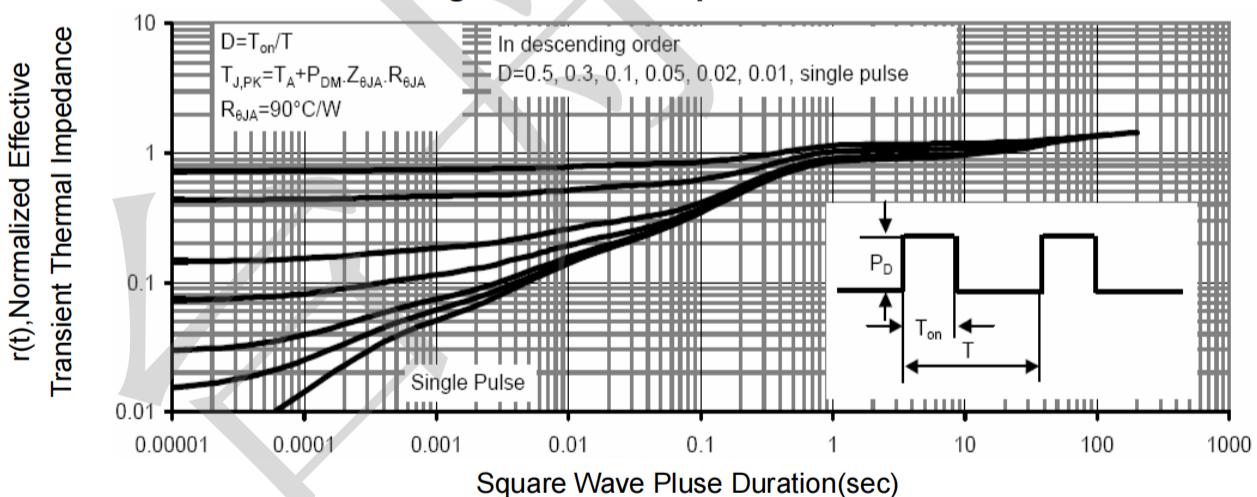
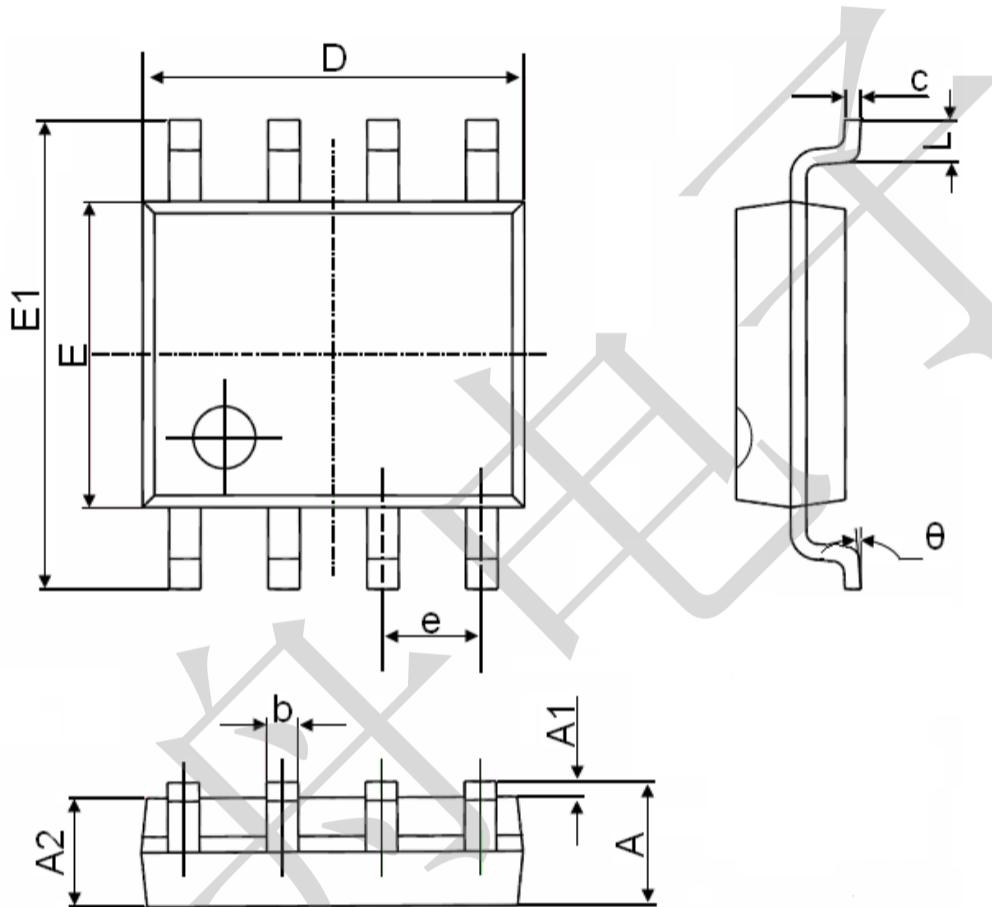


Figure 14 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°